Silicon PNP transistor epitaxial type
B5858

[Applications]

Portable radio 2W output amplifier of class-B push-pull operation
Medium power switching and muting

[Feature]

Correspond to SS8550
High collector current IC= -1.5A
Complimentary pair with phenitec P/N D5858

[Absolute maximum ratings (Ta=25C)]

Characteristic	Symbol	Maximum ratings	Unit
Collector-base voltage	VCBO	-40	V
Collector-emitter voltage	VCEO	-25	V
Emitter-base voltage	VEBO	-6	V
Collector current	IC	-1.5	A
Junction temperature	Tj	150	C
Storage temperature	Tstg	-55 to 150	C

[Electrical characteristics (Ta=25C)]

Characteristic	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BVCBO	-40	-	-	V	IC= -100uA, IE= 0A
Collector-emitter breakdown voltage	BVCEO	-25	-	-	V	IC= -2mA, IB= 0A
Emitter-base breakdown voltage	BVEBO	-6	-	-	V	IE= -100uA, IC= 0A
Collector cut-off current	ICBO	-	-	-100	nA	VCB= -40V, IE= 0A
Emitter cut-off current	IEBO	-	-	-100	nA	VEB= -6V, IE= 0A
DC current gain 1	hFE 1	45	-	-	-	VCE= -1V, IC= -5mA
DC current gain 2	hFE 2	85	160	300	-	VCE= -1V, IC= -100mA
DC current gain 3	hFE 3	40	-	-	-	VCE= -1V, IC= -800mA
Collector-emitter saturation voltage	VCE(sat)	-	-0.28	-0.5	V	IC= -800mA, IB= -80mA
Base-emitter saturation voltage	VBE(sat)	-	-0.98	-1.2	V	IC= -800mA, IB= -80mA
Base-emitter on voltage	VBE(on)	-	-0.66	-1	V	VCE= -1V, IC= -10mA
Transition frequency	fT	100	270	-	MHz	VCE= -10V, IE= 50mA
Collector output capacitance	Cob	-	6.5	-	pF	VCB= -10V, f = 1MHz, IE= 0A

Notice 1) These are measured data of transistors assembled by PHENITEC SEMICONDUCTOR Corp. and are for reference only.

Notice 2) The contents described herein are subject to change without notice.

Fig.1 hFE - IC
at VCE= -1V, Ta=25C

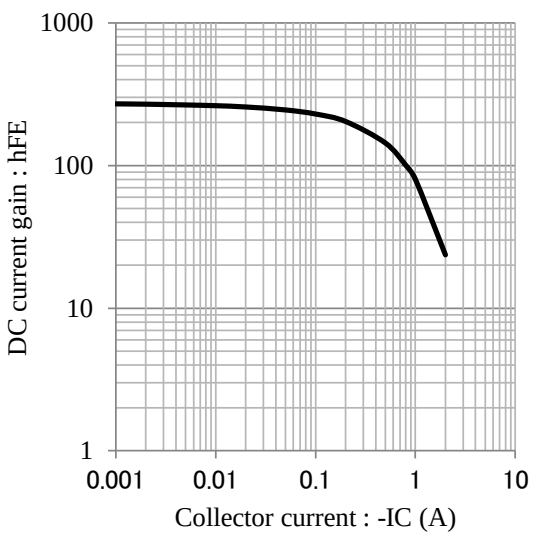

Fig.2 VCE(sat) - IC
at IC/IB=10, Ta=25C

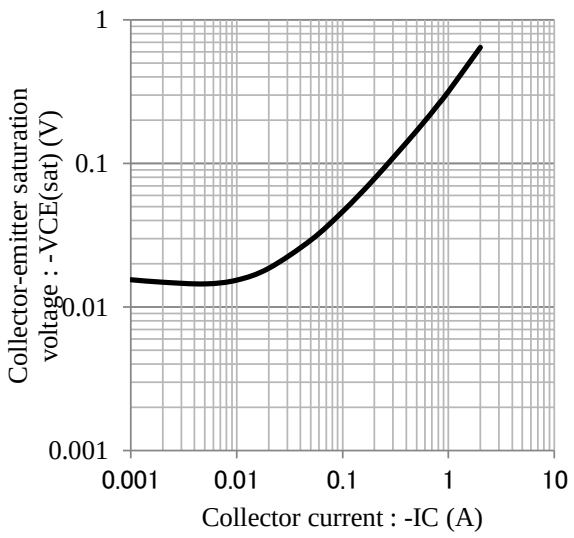

Fig.3 VBE(sat) - IC
at IC/IB=10, Ta=25C

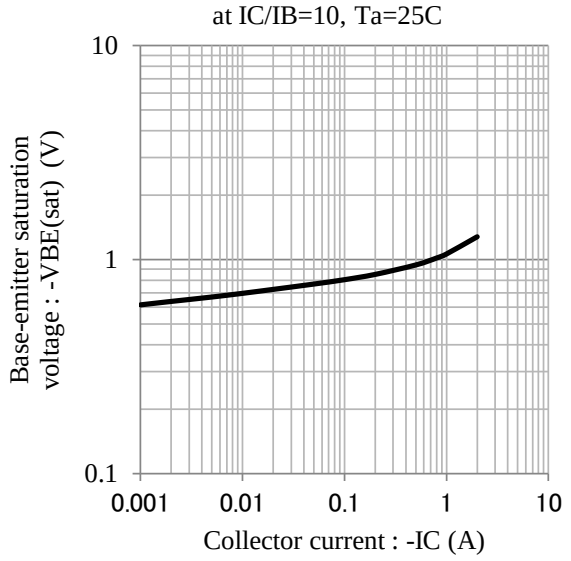

Fig.4 fT - IE
at VCE=-10V, Ta=25C

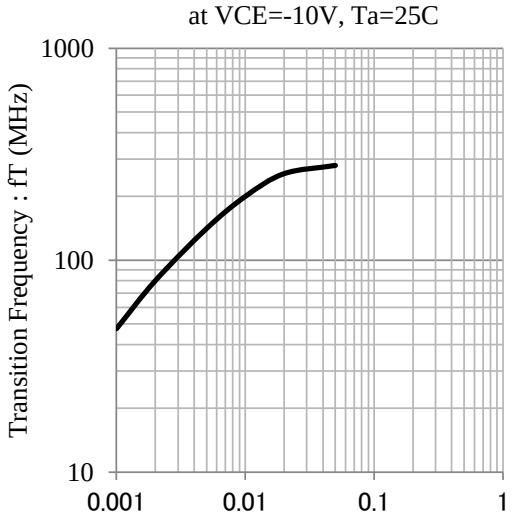

Fig.5 Cob - VCB
at f=1MHz, Ta=25C

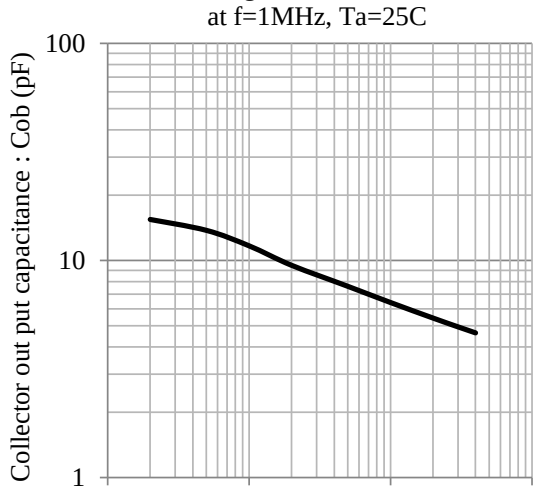

Fig.6 Cib - VEB
at f=1MHz,Ta=25C